

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

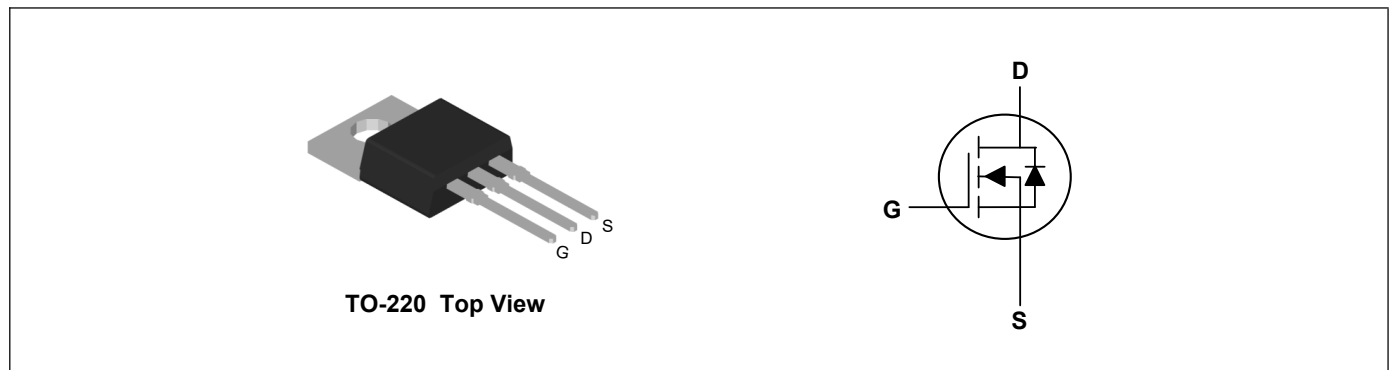
Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

Product Summary



V_{DS}	60	V
I_D	170	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	4.8	m Ω



Absolute Maximum Ratings($T_C=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, V_{GS} @ $10V^{1,6}$	$I_D@T_C=25^\circ\text{C}$	170	A
Continuous Drain Current, V_{GS} @ $10V^{1,6}$	$I_D@T_C=100^\circ\text{C}$	107	A
Continuous Drain Current, V_{GS} @ $10V^{1,6}$	$I_D@T_A=25^\circ\text{C}$	15	A
Continuous Drain Current, V_{GS} @ $10V^{1,6}$	$I_D@T_A=70^\circ\text{C}$	12	A
Pulsed Drain Current ²	I_{DM}	340	A
Single Pulse Avalanche Energy ³	EAS	245	mJ
Avalanche Current	I_{AS}	70	A
Total Power Dissipation ⁴	$P_D@T_C=25^\circ\text{C}$	260	W
Total Power Dissipation ⁴	$P_D@T_A=25^\circ\text{C}$	2.02	W
Storage Temperature Range	T_{STG}	-55 to 150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	62	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	0.48	$^\circ\text{C}/\text{W}$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	60	---	---	V
BV _{DSS} Temperature Coefficient	ΔBV _{DSS} /ΔT _J	Reference to 25°C, I _D =1mA	---	0.058	---	V/°C
Static Drain-Source On-Resistance ²	R _{DS(ON)}	V _{GS} =10V, I _D =30A	---	---	4.8	mΩ
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , I _D =250uA	2.5	---	4.5	V
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)}		---	-7.8	---	mV/°C
Drain-Source Leakage Current	I _{DSS}	V _{DS} =48V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =48V, V _{GS} =0V, T _J =55°C	---	---	5	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Forward Transconductance	g _{fs}	V _{DS} =5V, I _D =30A	---	50	---	S
Gate Resistance	R _g	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.4	---	Ω
Total Gate Charge	Q _g	V _{DS} =48V, V _{GS} =10V, I _D =15A	---	83.7	---	nC
Gate-Source Charge	Q _{gs}		---	28.6	---	
Gate-Drain Charge	Q _{gd}		---	29.3	---	
Turn-On Delay Time	T _{d(on)}	V _{DD} =30V, V _{GS} =10V, R _G =3.3Ω, I _D =48A	---	38.1	---	ns
Rise Time	T _r		---	73.3	---	
Turn-Off Delay Time	T _{d(off)}		---	51.6	---	
Fall Time	T _f		---	26.1	---	
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	5580	---	pF
Output Capacitance	C _{oss}		---	571	---	
Reverse Transfer Capacitance	C _{rss}		---	278	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ^{1,5}	I _S	V _G =V _D =0V, Force Current	---	---	170	A
Pulsed Source Current ^{2,5}	I _{SM}		---	---	340	A
Diode Forward Voltage ²	V _{SD}	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
Reverse Recovery Time	t _{rr}	I _F =30A, di/dt=100A/μs, T _J =25°C	---	27	---	nS
Reverse Recovery Charge	Q _{rr}		---	28	---	nC

Note:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V_{DD}=50V, V_{GS}=10V, L=0.1mH
- The power dissipation is limited by 150°C junction temperature
- The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.
- Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

Typical Characteristics

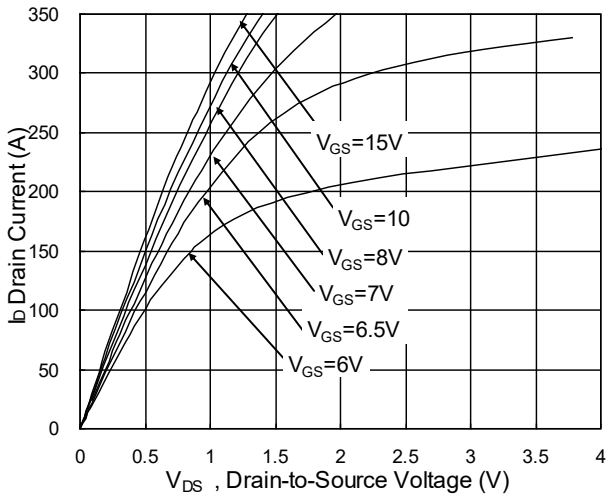


Fig.1 Typical Output Characteristics

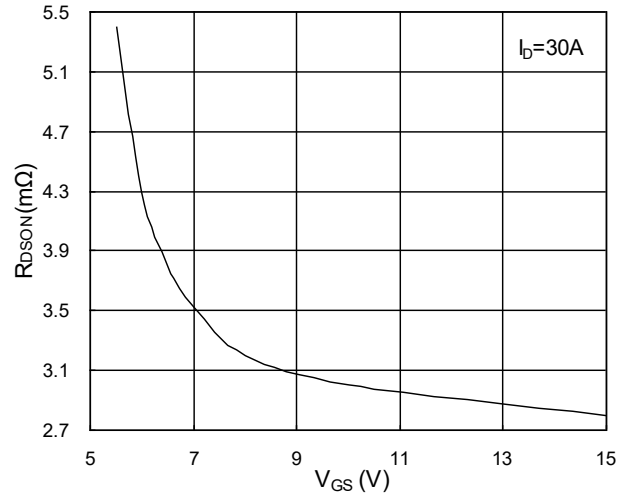


Fig.2 On-Resistance v.s Gate-Source

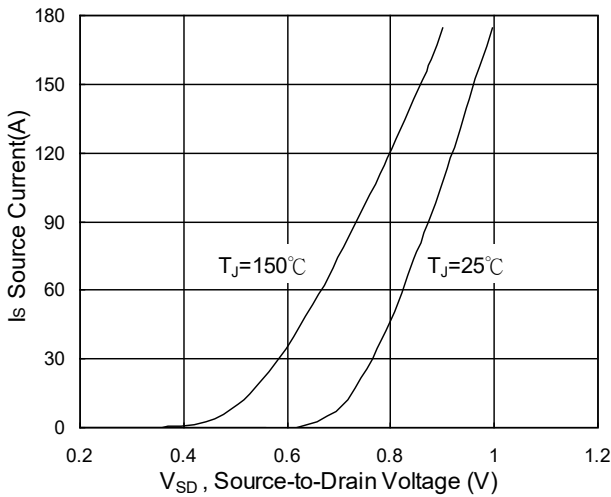


Fig.3 Forward Characteristics of Reverse

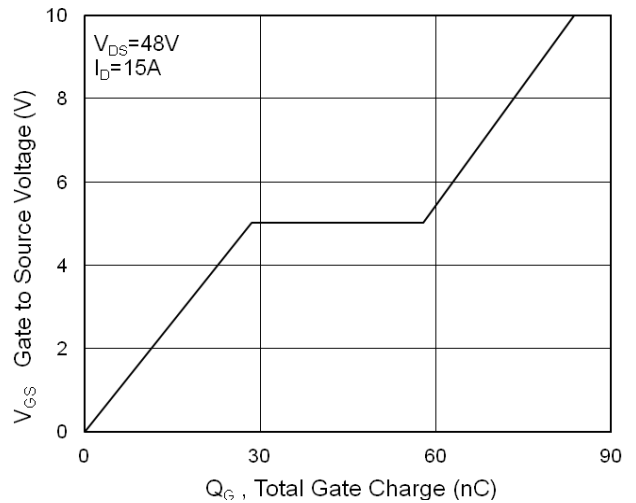


Fig.4 Gate-Charge Characteristics

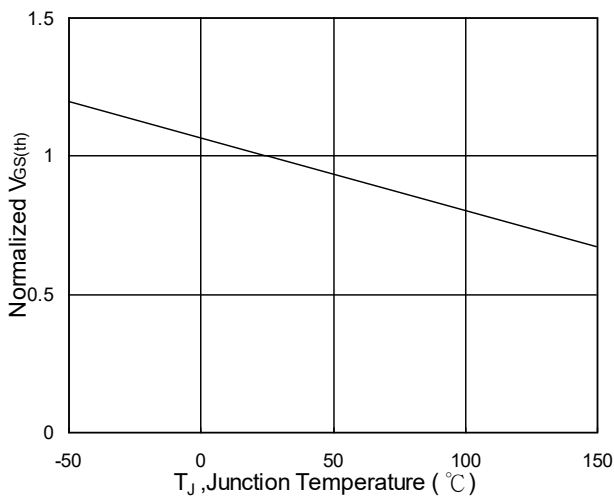


Fig.5 Normalized V_{GS(th)} v.s T_J

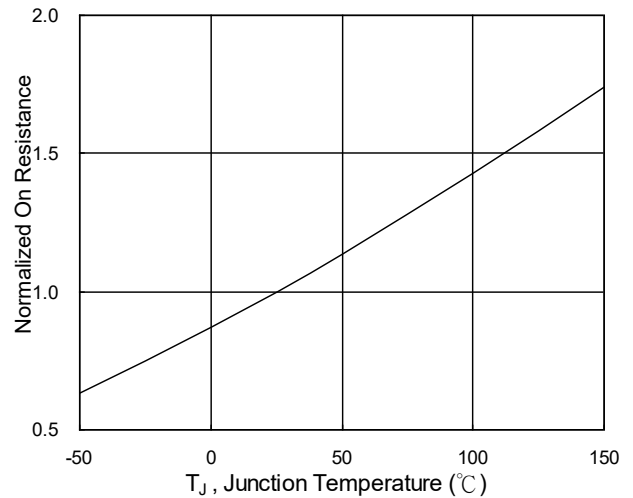


Fig.6 Normalized R_{DS(on)} v.s T_J

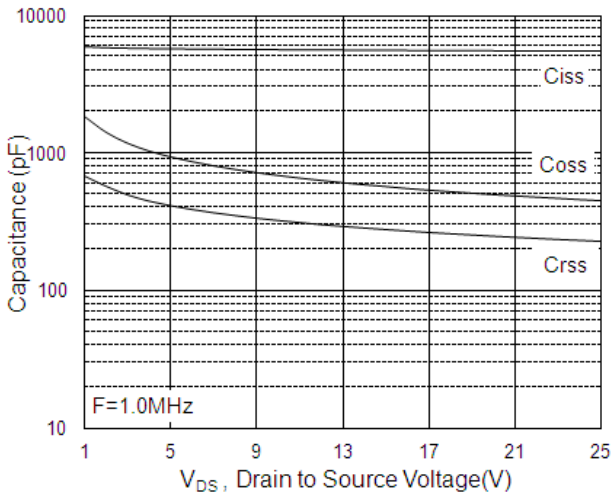


Fig.7 Capacitance

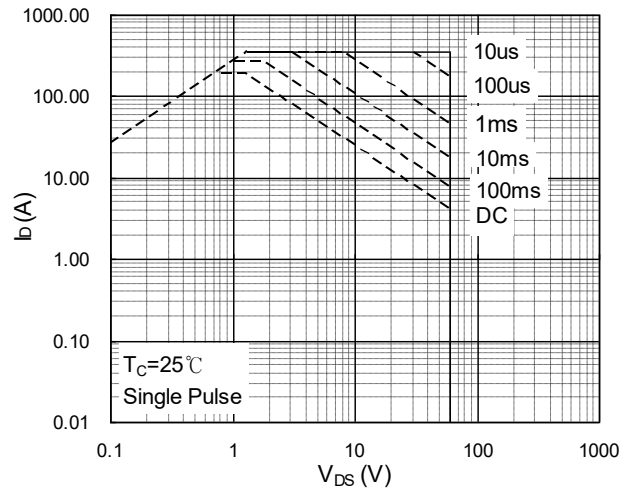


Fig.8 Safe Operating Area

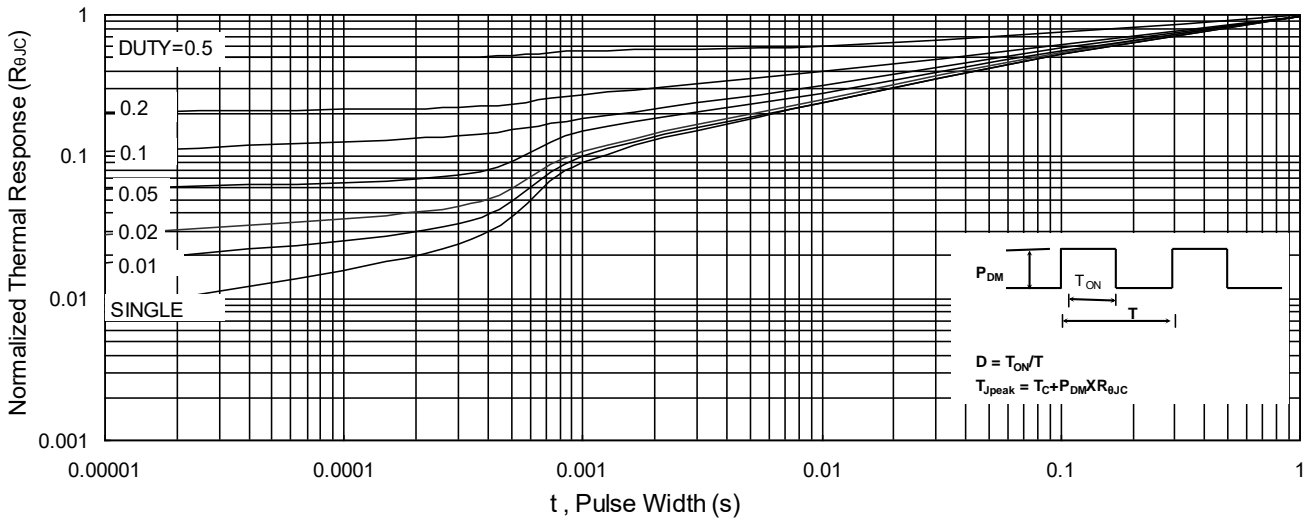


Fig.9 Normalized Maximum Transient Thermal Impedance

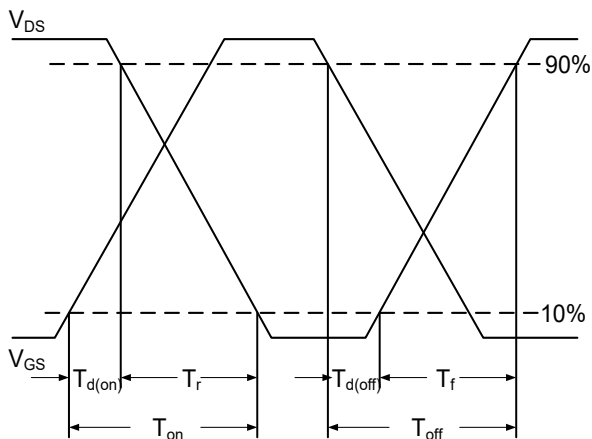


Fig.10 Switching Time Waveform

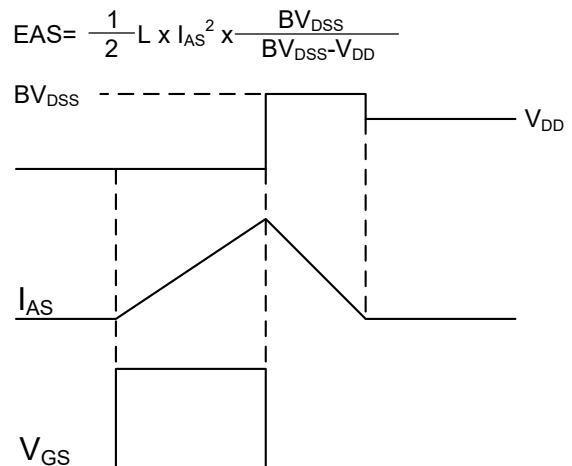
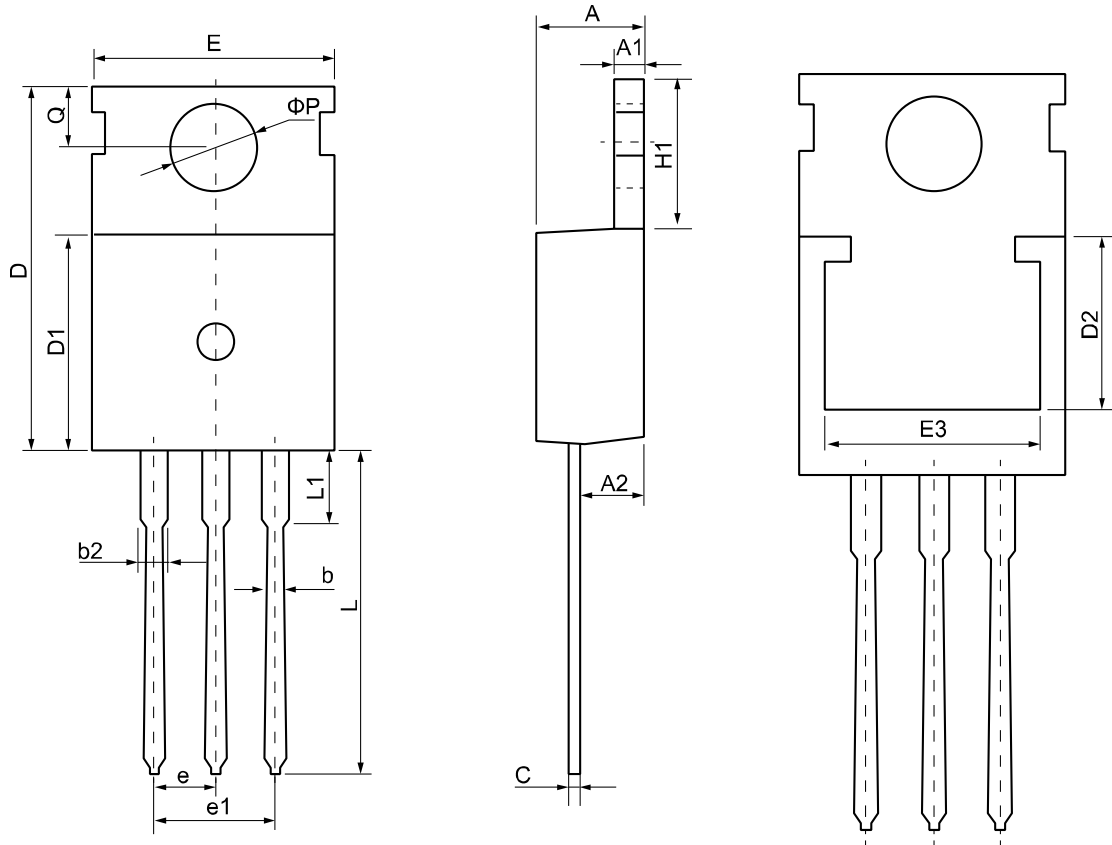


Fig.11 Unclamped Inductive Switching Waveform

TO-220 Package Outline Dimensions



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
A	4.30	4.55	4.75	E	9.65	10.00	10.25
A1	1.15	1.30	1.45	E3	7.00	--	--
A2	2.20	2.40	2.60	e	2.54 BSC		
b	0.70	0.80	0.95	e1	5.08 BSC		
b2	1.17	1.27	1.47	H1	6.30	6.50	6.80
c	0.40	0.50	0.65	L	12.70	13.50	14.10
D	15.30	15.60	15.90	L1	--	3.20	3.95
D1	8.90	9.10	9.35	phi P	3.40	3.60	3.80
D2	5.50	--	--	Q	2.60	2.80	3.00